

NPN Silicon AF Transistor Array

- For AF stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP transistors in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

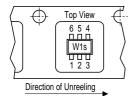


Type

BC817UPN

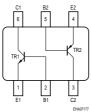


Tape loading orientation



Marking on SC74 package (for example W1s) corresponds to pin 1 of device

Posit орро



ition in tape: pin 1 osite of feed hole side		E1	B1 C2 EHAOS	7177					
	SC74_Tape								
	Marking		Р	in Conf	figurati	Package			
	1Bs	1=F1	2=R1	3=C2	4=F2	5=B2	6=C1	SC74	

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	45	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Collector current	I _C	500	mA
Peak collector current, $t_p \le 10 \text{ ms}$	I _{CM}	1000	
Base current	I _B	100	
Peak base current	I _{BM}	200	
Total power dissipation-	P _{tot}	330	mW
<i>T</i> _S ≤ 115 °C			
Junction temperature	T_{i}	150	°C
Storage temperature	T _{stq}	-65 150	



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 105	K/W

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				•	
Collector-emitter breakdown voltage	V _{(BR)CEO}	45	-	-	V
$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	_	
$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$					
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5	-	-	
$I_{\rm E} = 10 \ \mu \text{A}, \ I_{\rm C} = 0$					
Collector-base cutoff current	I _{CBO}				μA
$V_{\rm CB} = 25 \text{ V}, I_{\rm E} = 0$		-	-	0.1	
$V_{\rm CB}$ = 25 V, $I_{\rm E}$ = 0 , $T_{\rm A}$ = 150 °C		-	-	50	
Emitter-base cutoff current	I _{EBO}	-	-	100	nA
$V_{\rm EB} = 4 \text{ V}, I_{\rm C} = 0$					
DC current gain ²⁾	h _{FE}				-
$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 1 V		160	250	400	
$I_{\rm C}$ = 300 mA, $V_{\rm CE}$ = 1 V		100	-	-	
Collector-emitter saturation voltage ²⁾	V _{CEsat}	-	-	0.7	V
$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 50 mA					
Base emitter saturation voltage ²⁾	V _{BEsat}	-	-	1.2	
$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 50 mA					
AC Characteristics					
Transition frequency	f _T	-	170	-	MHz
$I_{\rm C}$ = 50 mA, $V_{\rm CE}$ = 5 V, f = 100 MHz					
Collector-base capacitance	C _{cb}	-	6	-	pF
$f = 1 \text{ MHz}, V_{BE} = 10 \text{ V}$					
Emitter-base capacitance	C _{eb}	-	60	-	
$V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$					

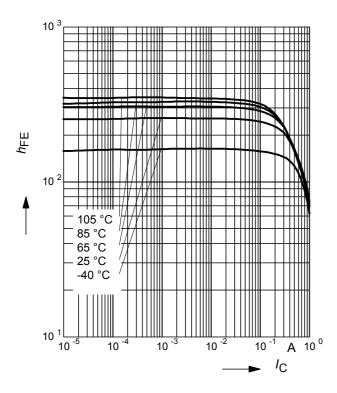
 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

 $^{^{2}}$ Pulse test: t < 300µs; D < 2%



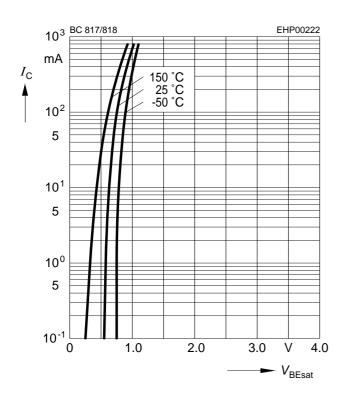
DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 1 \text{ V}$$



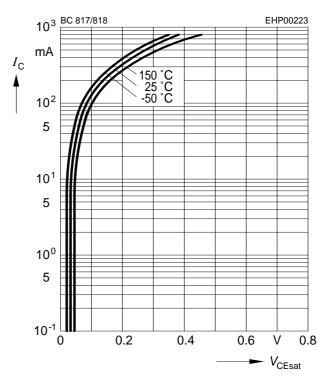
Base-emitter saturation voltage

$$I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$$



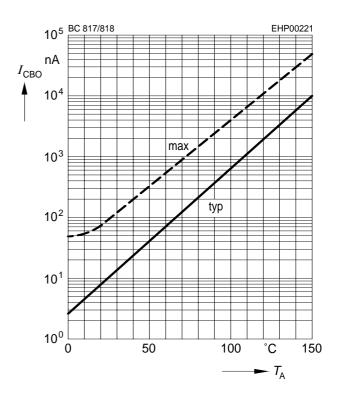
Collector-emitter saturation voltage

$$I_{\text{C}} = f(V_{\text{CEsat}}), h_{\text{FE}} = 10$$



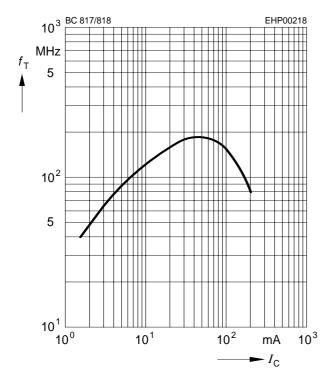
Collector cutoff current $I_{CBO} = f(T_A)$

$$V_{\rm CBO}$$
 = 25 V

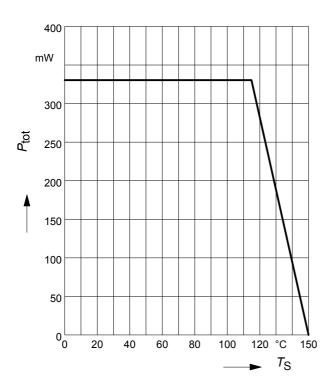




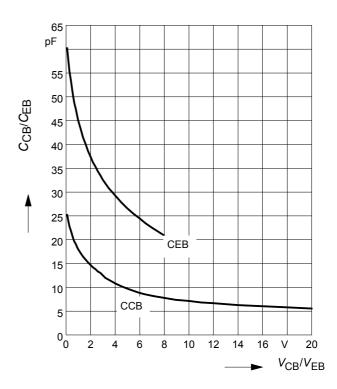
Transition frequency $f_T = f(I_C)$ V_{CE} = parameter in V, f = 2 GHz



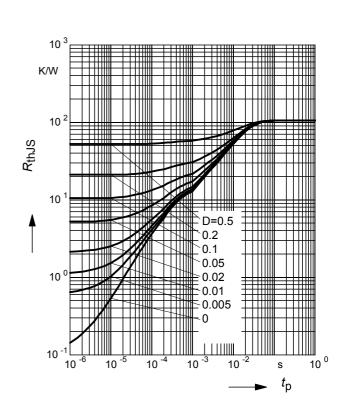
Total power dissipation $P_{tot} = f(T_S)$



Collector-base capacitance $C_{cb} = f(V_{CB})$ Emitter-base capacitance $C_{eb} = f(V_{EB})$



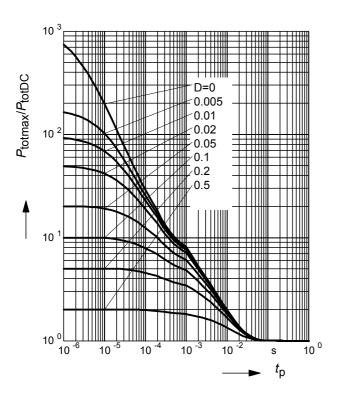
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

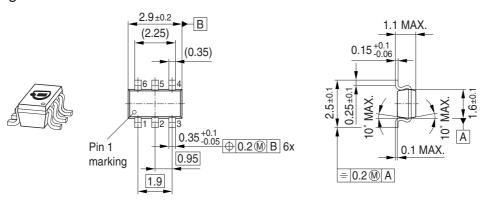
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$



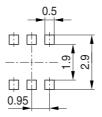
2011-09-15



Package Outline

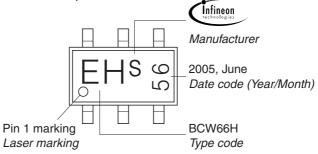


Foot Print



Marking Layout (Example)

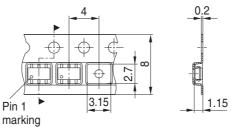
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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